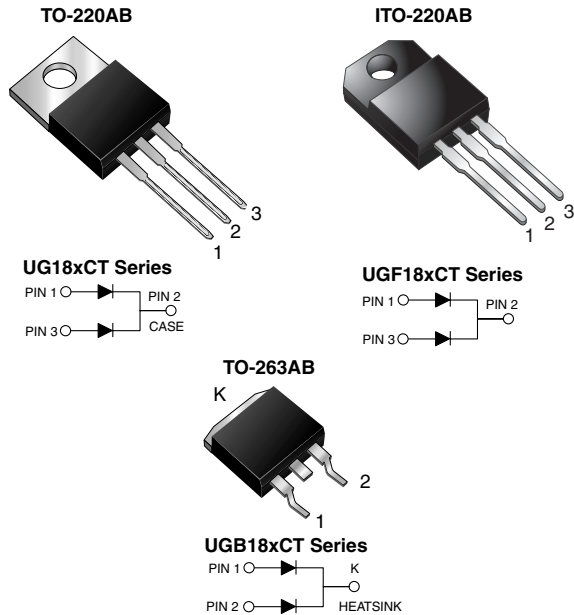


Dual Common-Cathode Ultrafast Plastic Rectifier



FEATURES

- Glass passivated chip junction
- Ultrafast recovery time
- Low switching losses, high efficiency
- Low forward voltage drop
- High forward surge capability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder dip 260 °C, 40 s (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency rectifier of switching mode power supplies, inverters, freewheeling diodes, dc-to-dc converters, and other power switching application.

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	18 A
V_{RRM}	50 V to 200 V
I_{FSM}	175 A
t_{rr}	20 ns
V_F	0.95 V
$T_J \text{ max.}$	150 °C

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS ($T_C = 25 \text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	UG18ACT	UG18BCT	UG18CCT	UG18DCT	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	150	200	V
Maximum RMS voltage	V_{RMS}	35	70	105	140	V
Maximum DC blocking voltage	V_{DC}	50	100	150	200	V
Maximum average forward rectified current at $T_C = 105 \text{ °C}$	$I_{F(AV)}$	18				A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	175				A
Operating junction and storage temperature range	T_J, T_{STG}	- 65 to + 150				°C
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1 \text{ min}$	V_{AC}	1500				V

UG(F,B)18ACT thru UG(F,B)18DCT

Vishay General Semiconductor

ELECTRICAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted)								
PARAMETER	TEST CONDITIONS		SYMBOL	UG18ACT	UG18BCT	UG18CCT	UG18DCT	UNIT
Maximum instantaneous forward voltage per diode (1)	9.0 A 20 A 5.0 A	T _J = 100 °C	V _F		1.1 1.2 0.95			V
Maximum DC reverse current at rated DC blocking voltage per diode		T _A = 25 °C T _A = 100 °C	I _R		10 300			μA
Maximum reverse recovery time per diode	I _F = 0.5 A, I _R = 1.0 A, I _{rr} = 0.25 A		t _{rr}		20			ns
Maximum reverse recovery time per diode	I _F = 9.0 A, V _R = 30 V, dI/dt = 50 A/μs, I _{rr} = 10 % I _{RM}	T _J = 25 °C T _J = 100 °C	t _{rr}		30 50			ns
Maximum stored charge per diode	I _F = 9.0 A, V _R = 30 V, dI/dt = 50 A/μs, I _{rr} = 10 % I _{RM}	T _J = 25 °C T _J = 100 °C	Q _{rr}		20 45			nC
Typical junction capacitance per diode	at 4.0 V, 1 MHz		C _J		30			pF

Note:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	UG18	UGF18	UGB18	UNIT
Typical thermal resistance from junction to case per diode	R _{θJC}	4.0	6.0	4.0	°C/W

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ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	UG18DCT-E3/45	1.85	45	50/tube	Tube
ITO-220AB	UGF18DCT-E3/45	2.00	45	50/tube	Tube
TO-263AB	UGB18DCT-E3/45	1.35	45	50/tube	Tube
TO-263AB	UGB18DCT-E3/81	1.35	81	800/reel	Tape and reel
TO-220AB	UG18DCTHE3/45 (1)	1.85	45	50/tube	Tube
ITO-220AB	UGF18DCTHE3/45 (1)	2.00	45	50/tube	Tube
TO-263AB	UGB18DCTHE3/45 (1)	1.35	45	50/tube	Tube
TO-263AB	UGB18DCTHE3/81 (1)	1.35	81	800/reel	Tape and reel

Note:

(1) Automotive grade AEC Q101 qualified



RATINGS AND CHARACTERISTICS CURVES

($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

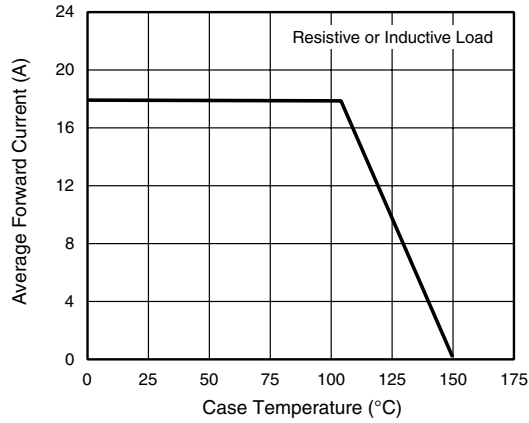


Figure 1. Forward Current Derating Curve

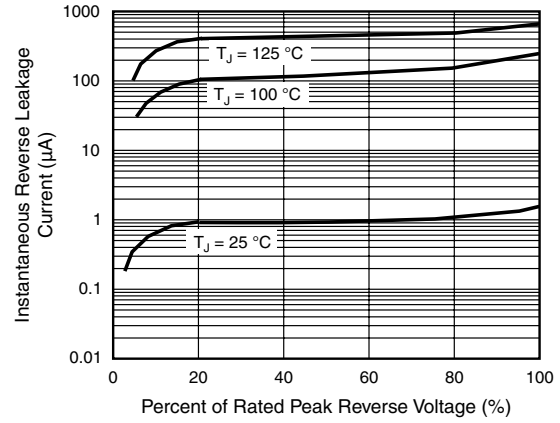


Figure 4. Typical Reverse Leakage Characteristics Per Diode

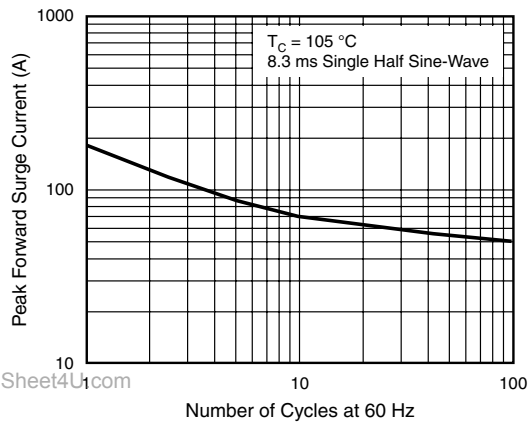


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

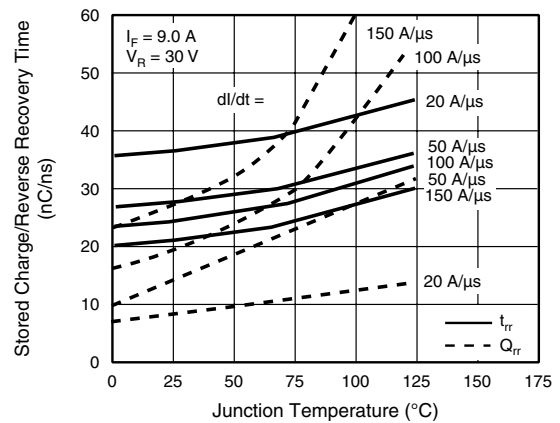


Figure 5. Reverse Switching Characteristics Per Diode

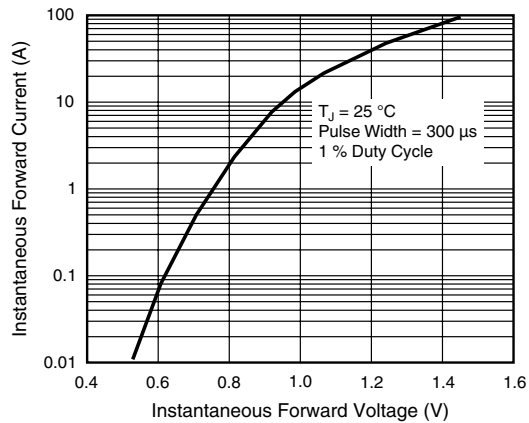


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

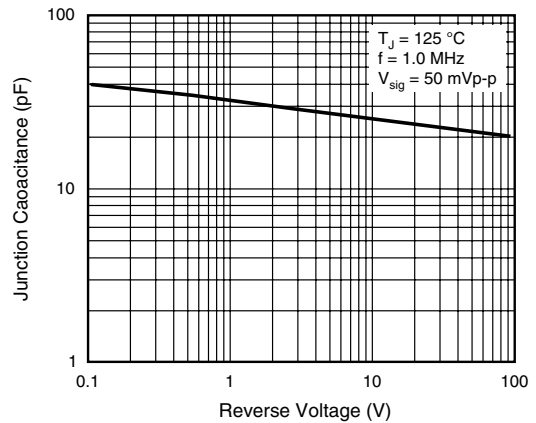


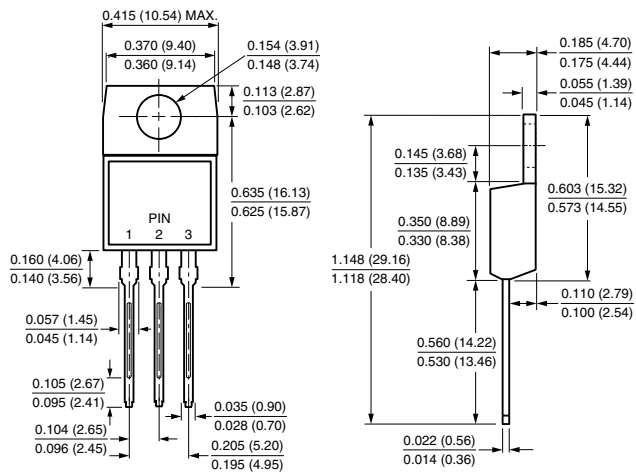
Figure 6. Typical Junction Capacitance Per Diode

UG(F,B)18ACT thru UG(F,B)18DCT

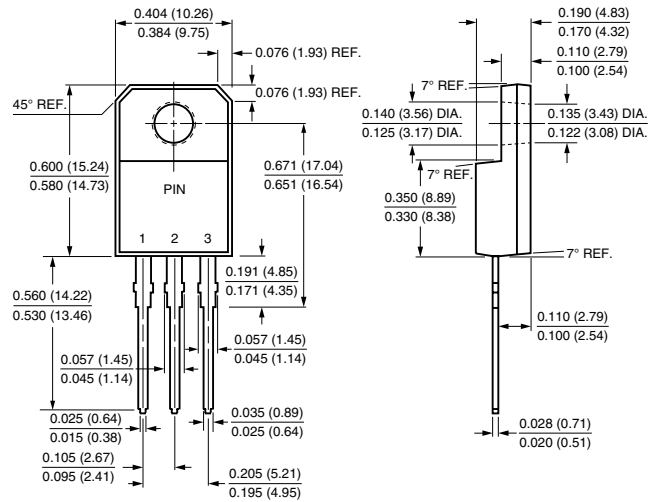
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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

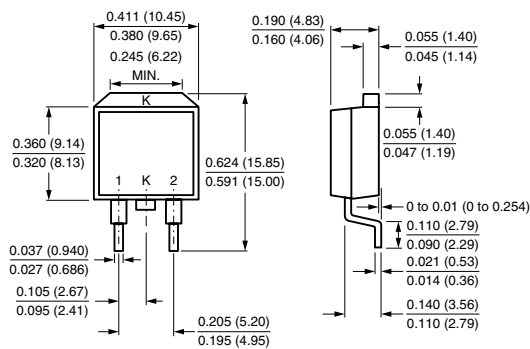
TO-220AB



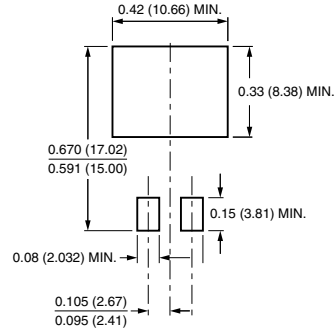
ITO-220AB



TO-263AB



Mounting Pad Layout





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All product specifications and data are subject to change without notice.

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